Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (previously presented): A sputtering target comprising a target containing at least Co, Cr, Pt and B and having a target surface prepared by melting, casting, rolling, cutting and polishing in which intermetallic compounds, oxides, carbides, carbonitrides and other substances without ductility exist in a highly ductile matrix phase of said sputtering target at a volume ratio of 1 to 50%, said substances without ductility being of a size in which an average particle diameter is at least 0.5 to 50μm, a Vickers hardness of said highly ductile matrix phase being 400 or less, a Vickers hardness of said substances without ductility being 400 or more, and a hardness difference thereof being at least 1.5 times, wherein surface defects of 10μm or more resulting from machine work do not exist.

Claims 2-3 (canceled).

Claim 4 (currently amended): A surface processing method for a sputtering target, comprising the steps of:

preparing a target surface of a sputtering target containing at least Co, Cr, Pt and B by melting, casting and rolling in which intermetallic compounds, oxides, carbides, carbonitrides and other substances without ductility exist in a highly ductile matrix phase of said target at a volume ratio of 1 to 50%, said substances without ductility being of a size in which an average

particle diameter is at least 0.5 to 50μm, a Vickers hardness of said highly ductile matrix phase being 400 or less, a Vickers hardness of said substances without ductility being 400 or more, and a hardness difference thereof being at least 1.5 times;

preliminarily subjecting said target to primary processing of cutting work by cutting a thickness of 1mm to 10mm from said target surface; and

then subsequently finish processing said target ~~via~~, said finishing processing step consisting of polishing a thickness of 1μm to 50μm from said target surface with sandpaper or a grindstone having a rough abrasive grain size of #80 to #400 after said primary processing such that surface defects of 10μm or more resulting from machine work do not exist.

Claims 5-11 (canceled).

Claim 12 (previously presented): A surface processing method according to claim 4, wherein said cutting is performed with lathe processing employing a cutting tool or a chip.

Claim 13 (previously presented): A sputtering target, comprising:

a sputtering target body prepared by melting, casting, rolling, cutting and polishing and containing at least Co, Cr, Pt and B;

said sputtering target body having a surface including particles of intermetallic compounds, oxides, carbides, and carbonitrides existing within a highly ductile matrix phase at a volume ratio of 1 to 50%;

said particles of intermetallic compounds, oxides, carbides, and carbonitrides having an average particle diameter of at least 0.5μm;

said matrix phase having a Vickers hardness of 400 or less, said particles of intermetallic compounds, oxides, carbides, and carbonitrides having a Vickers hardness of 400 or more, and a hardness difference thereof being at least 1.5 times; and

surface defects of 10μm or more resulting from machine work performed on said sputtering target body do not exist on said surface and said surface provides a flat and smooth target face without undulation.

Claim 14 (previously presented): A sputtering target according to claim 13, wherein said average particle diameter of said intermetallic compounds, oxides, carbides, and carbonitrides is 0.5 to 50μm.

Claim 15 (previously presented): A sputtering target according to claim 14, wherein said intermetallic compounds, oxides, carbides, and carbonitrides are less ductile than said matrix phase.

Claim 16 (previously presented): A sputtering target according to claim 14, wherein said intermetallic compounds, oxides, carbides, and carbonitrides are without ductility.

Claim 17 (currently amended): A method of processing a surface of a sputtering target, ~~comprising~~ consisting of the steps of:

melting, casting and rolling raw material containing at least Co, Cr, Pt and B to form a sputtering target having a surface with particles of intermetallic compounds, oxides, carbides, and carbonitrides existing within a highly ductile matrix phase at a volume ratio of 1 to 50%, the intermetallic compounds, oxides, carbides, and carbonitrides having an average particle diameter of at least 0.5μm and a Vickers hardness of 400 or more, the matrix phase having a Vickers hardness of 400 or less, and a hardness difference thereof being at least 1.5 times;

preliminarily subjecting said sputtering target to primary processing of cutting work by cutting 1mm to 10mm of depth from said target surface; and

then subsequently finish processing said sputtering target via polishing 1μm to 50μm of depth from said surface with sandpaper or a grindstone having a rough abrasive grain size of #80 to #400 after said primary processing such that surface defects of 10μm or more resulting from machine work do not exist and such that the target surface provides a flat and smooth target face without undulation.